A1 Contd Sub B7

66. (New) A method of protecting conductive elements of a circuit from corrosive effects of an upper circuit element while electrically connecting the upper circuit element with a lower circuit element, the method comprising:

forming a silicon nitride barrier liner around a conductive electrical connector which electrically connects an upper circuit element to a lower circuit element, thereby protecting the conductive electrical connector from corrosive effects of the upper circuit element; and

forming an insulating barrier liner around at least one gate formed on the lower circuit element, wherein the insulating barrier liner contacts the silicon nitride barrier liner.

67. (New) The method of Claim 66, wherein portions of the gate contact the silicon nitride barrier liner.

68. (New) The method of Claim 66, wherein the insulating barrier liner comprises silicon nitride.

69. (New) The method of Claim 66, further comprising:

forming a conductive barrier liner around the conductive electrical connector, wherein sidewalls of the conductive barrier liner are between the silicon nitride barrier liner and the conductive electrical connector and a cap portion of the conductive barrier liner is above the conductive electrical connector and forms part of the electrical connection between the upper circuit element and the lower circuit element.

70. (New) The method of Claim 66, wherein the upper circuit element comprises a capacitor including a dielectric material having a dielectric constant greater than about 10.

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71. (New) The method of Claim 66, wherein the upper circuit element comprises a memory cell capacitor and the lower circuit element comprises a substrate including an active area electrically connected to the conductive electrical connector.

72. (New) A method of electrically connecting a capacitor having a high dielectric constant dielectric to a transistor active area of a substrate while protecting the electrical connection from corrosive aspects of the high dielectric constant dielectric, the method comprising:

surrounding sidewalls of a conductive contact plug which electrically connects a capacitor having a high dielectric constant dielectric to a transistor active area of a substrate, with a first barrier to corrosion, wherein the first barrier comprises a conductive material; and

surrounding sidewalls of the first barrier with a second barrier to corrosion, wherein the second barrier comprises insulating material, thereby forming at least two protective barriers around the conductive contact plug to avoid the corrosive aspects of the capacitor.

73. (New) The method of Claim 72, further comprising surrounding a side of the conductive contact plug opposite the transistor active area with a third barrier to corrosion, wherein the third barrier comprises a conductive material and electrically connects the capacitor with the contact conductive contact plug.

74. (New) The method of Claim 72, further comprising surrounding a side of the conductive contact plug nearest the transistor active area with a third barrier to corrosion, wherein the third barrier comprises a conductive material and electrically connects the transistor active area with the contact conductive contact plug.

75. (New) The method of Claim 72, further comprising surrounding at least one of a bit line or a word line on the substrate with an insulating layer including a sidewall portion and a cap portion.